

Feature

- Stud Cathode normal
- Zener diode
- Low leakage current
- Fast response speed
(from 0V to V_{BR} response time less than 1ps)
- Glass passivated junction
- Excellent clamping capability
- withstand 5000w peak pulse (10/1000 μ s)



DO-5



Applications

- Sensitive electronic device protection
- Protection of I/O Interfaces, V_{CC} bus
- Protection of vulnerable circuits used in telecom
- Protection computer, industrial and consumer

Max Rating($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter		Value	Unit
P_{PPM}	Peak Pulse Power Dissipation by 10/1000 μ s waveform		5000	W
$PM(AV)$	Steady state Power Dissipation	$T_A=25^{\circ}\text{C}$	100	W
		$T_A=65^{\circ}\text{C}$	75	W
I_F	forward current(not1)		6	A
I_{FSM}	Peak forward surge current		12	A
T_J	Operating Junction Ranges		-55 to 175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Ranges		-55 to 150	$^{\circ}\text{C}$
Weight	Excluding mounting kit(approx)		14	g
Torque	Screw standard:M6		3.4	N·m

Electrical Characteristics($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Value			Unit
			Min	Type	Max	
V_{RWM}	Reverse Stand off Voltage			20		V
V_{BR}	Breakdown Voltage	@ I_T , (not2)	22		24.4	V
I_T	Test Current			5		mA
I_{PP}	Maximum Peak Pulse Current		155			A

V_C	Maximum Clamping Voltage	@ I_{PP} , Continue 20ms		32.4		V
I_R	Maximum Reverse Leakage Current	@ V_{RWM}			1.58	μA

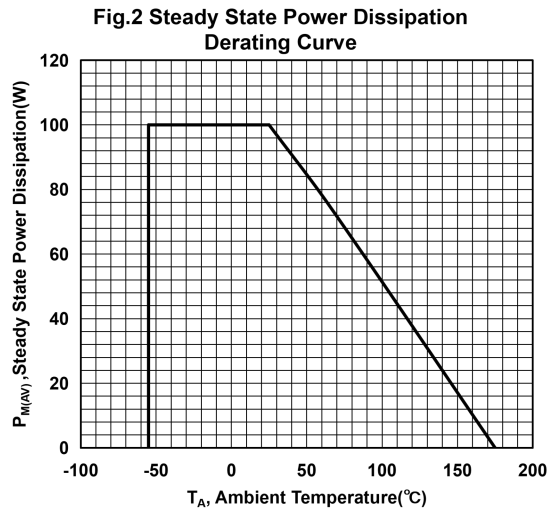
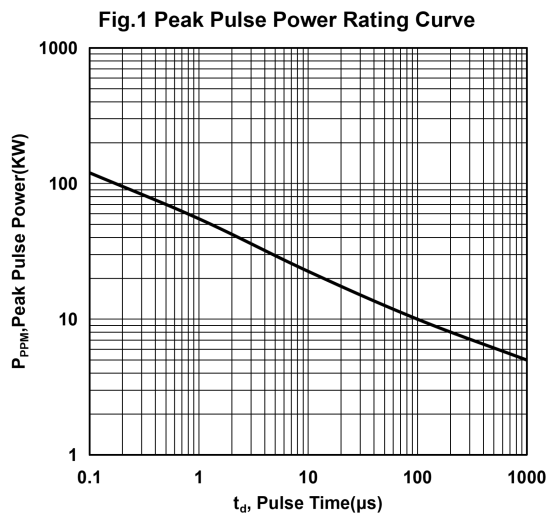
Note:

2. Pulse $\leq 100\mu s$, duty cycle ≤ 0.001

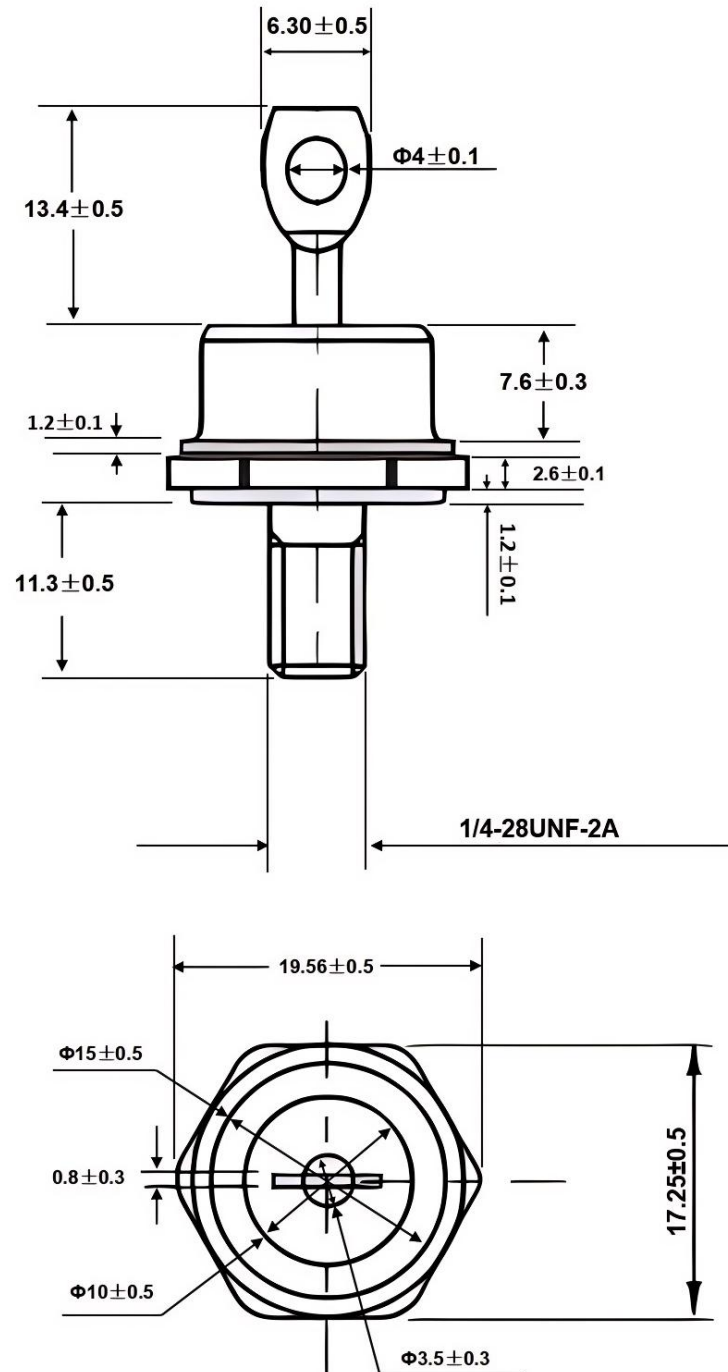
Thermal Characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$R_{th(j-c)}$	Thermal Resistance Junction to Case	DO-5	-	1.1	-	$^{\circ}C/W$

Electrical characteristics(Curves)



Package Dimension(DO-5)



For metric devices:M6x1

Unit:mm

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